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(54) Title: SYSTEMS AND METHODS FOR SELECTIVE TUNGSTEN DEPOSITION IN VIAS

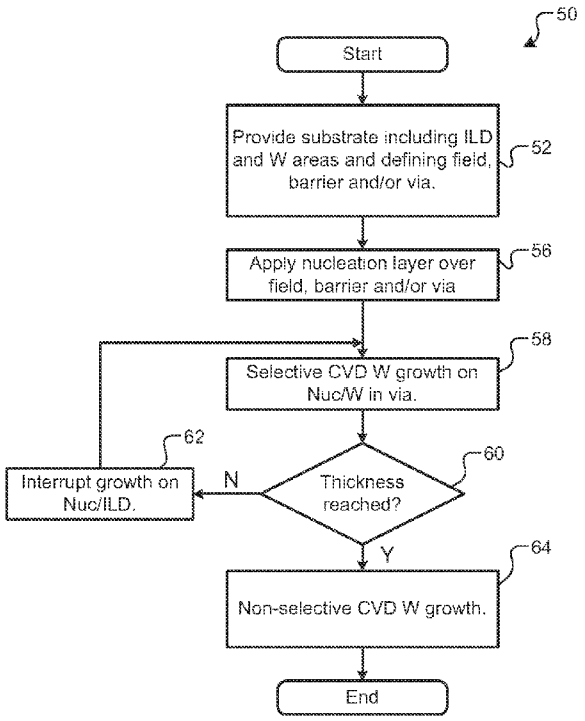


FIG. 2C

(57) Abstract: A method for processing a substrate includes providing a substrate including a metal layer, a dielectric layer arranged on the metal layer, and at least one of a via and a trench formed in the dielectric layer; depositing a metal using chemical vapor deposition (CVD) during a first deposition period, wherein the first deposition period is longer than a first nucleation period that is required to deposit the metal on the metal layer; stopping the first deposition period prior to a second nucleation delay period, wherein the second nucleation period is required to deposit the metal on the dielectric layer; performing the depositing and the stopping N times, where N is an integer greater than or equal to one; and after the performing, depositing the metal using CVD during a second deposition period that is longer than the second nucleation delay period

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